

**Features**

- Fast Read Access Time - 120 ns
- Fast Byte Write - 200  $\mu$ s or 1 ms
- Self-Timed Byte Write Cycle
  - Internal Address and Data Latches
  - Internal Control Timer
  - Automatic Clear Before Write
- Direct Microprocessor Control
  - READY/BUSY Open Drain Output
  - DATA Polling
- Low Power
  - 30 mA Active Current
  - 100  $\mu$ A CMOS Standby Current
- High Reliability
  - Endurance:  $10^4$  or  $10^5$  Cycles
  - Data Retention: 10 years
- 5 V  $\pm$  10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Approved Byte-Wide Pinout
- Full Military, Commercial, and Industrial Temperature Ranges

**64K (8K x 8)**  
**CMOS**  
**E<sup>2</sup>PROM**

**Description**

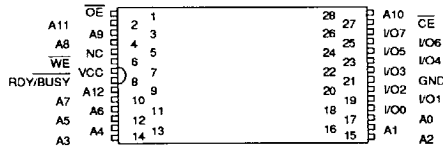
The AT28C64 is a low-power, high-performance 8,192 words x 8 bit nonvolatile Electrically Erasable and Programmable Read Only Memory with popular, easy to use features. The device is manufactured with Atmel's reliable nonvolatile technology.

The AT28C64 is accessed like a Static RAM for the read or write cycles without the need for external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a

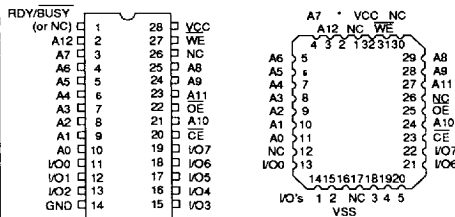
*(continued on next page)*

**Pin Configurations**

TSOP Top View



Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
OE	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
RDY/BUSY	Ready/Busy Output
NC	No Connect



\* = RDY/BUSY (or NC)

Note: PLCC package pins 1 and 17 are DON'T CONNECT.



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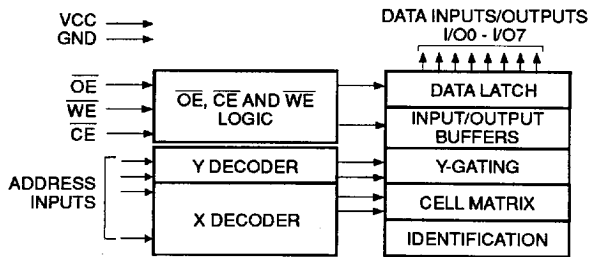
## Description (Continued)

write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The device includes two methods for detecting the end of a write cycle, level detection of RDY/ $\overline{\text{BUSY}}$  (unless pin 1 is N.C.) and  $\overline{\text{DATA}}$  polling of I/O7. Once the end of a write cycle has been detected, a new access for a read or write can begin.

The CMOS technology offers fast access times of 150 ns at low power dissipation. When the chip is deselected the standby current is less than 100  $\mu\text{A}$ .

Atmel's 28C64 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of E<sup>2</sup>PROM are available for device identification or tracking.

## Block Diagram



## Absolute Maximum Ratings\*

Temperature Under Bias.....	-55°C to +125°C
Storage Temperature.....	-65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground .....	-0.6 V to +6.25 V
All Output Voltages with Respect to Ground .....	-0.6 V to V <sub>CC</sub> +0.6 V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground .....	-0.6 V to +13.5 V

\*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Device Operation**

**READ:** The AT28C64 is accessed like a Static RAM. When  $\overline{CE}$  and  $\overline{OE}$  are low and  $\overline{WE}$  is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever  $\overline{CE}$  or  $\overline{OE}$  is high. This dual line control gives designers increased flexibility in preventing bus contention.

**BYTE WRITE:** Writing data into the AT28C64 is similar to writing into a Static RAM. A low pulse on the  $\overline{WE}$  or  $\overline{CE}$  input with  $\overline{OE}$  high and  $\overline{CE}$  or  $\overline{WE}$  low (respectively) initiates a byte write. The address location is latched on the falling edge of  $\overline{WE}$  (or  $\overline{CE}$ ); the new data is latched on the rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion.

**FAST BYTE WRITE:** The AT28C64F offers a byte write time of 200  $\mu$ s maximum. This feature allows the entire device to be rewritten in 1.6 seconds.

**READY/BUSY:** Pin 1 is an open drain  $\overline{RDY}/\overline{BUSY}$  output that can be used to detect the end of a write cycle.  $\overline{RDY}/\overline{BUSY}$  is actively pulled low during the write cycle and is released at the completion of the write. The open drain connection allows for OR-tying of several devices to the same  $\overline{RDY}/\overline{BUSY}$  line. Pin 1 is not connected for the AT28C64X.

**$\overline{DATA}$  POLLING:** The AT28C64 provides  $\overline{DATA}$  POLLING to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in the complement of that data for I/O<sub>7</sub> (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

**WRITE PROTECTION:** Inadvertent writes to the device are protected against in the following ways. (a) Vcc sense— if Vcc is below 3.8 V (typical) the write function is inhibited. (b) Vcc power on delay— once Vcc has reached 3.8 V the device will automatically time out 5 ms (typical) before allowing a byte write. (c) Write Inhibit— holding any one of  $\overline{OE}$  low,  $\overline{CE}$  high or  $\overline{WE}$  high inhibits byte write cycles.

**CHIP CLEAR:** The contents of the entire memory of the AT28C64 may be set to the high state by the CHIP CLEAR operation. By setting  $\overline{CE}$  low and  $\overline{OE}$  to 12 volts, the chip is cleared when a 10 msec low pulse is applied to  $\overline{WE}$ .

**DEVICE IDENTIFICATION:** An extra 32 bytes of E<sup>2</sup>PROM memory are available to the user for device identification. By raising A9 to 12  $\pm$  0.5 V and using address locations 1FE0H to 1FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

**Pin Capacitance** (f = 1 MHz, T = 25°C) <sup>(1)</sup>

	Typ	Max	Units	Conditions
C <sub>IN</sub>	4	6	pF	V <sub>IN</sub> = 0 V
C <sub>OUT</sub>	8	12	pF	V <sub>OUT</sub> = 0 V

Note: 1. This parameter is characterized and is not 100% tested.





## D.C. and A.C. Operating Range

		AT28C64-12	AT28C64-15	AT28C64-20	AT28C64-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
V <sub>CC</sub> Power Supply		5 V ± 10%	5 V ± 10%	5 V ± 10%	5 V ± 10%

## Operating Modes

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O
Read	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>
Write <sup>(2)</sup>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	D <sub>IN</sub>
Standby/Write Inhibit	V <sub>IH</sub>	X <sup>(1)</sup>	X	High Z
Write Inhibit	X	X	V <sub>IH</sub>	
Write Inhibit	X	V <sub>IL</sub>	X	
Output Disable	X	V <sub>IH</sub>	X	High Z
Chip Erase	V <sub>IL</sub>	V <sub>H</sub> <sup>(3)</sup>	V <sub>IL</sub>	High Z

Notes: 1. X can be V<sub>IL</sub> or V<sub>IH</sub>.

2. Refer to A.C. Programming Waveforms.

3. V<sub>H</sub> = 12.0 V ± 0.5 V.

## D.C. Characteristics

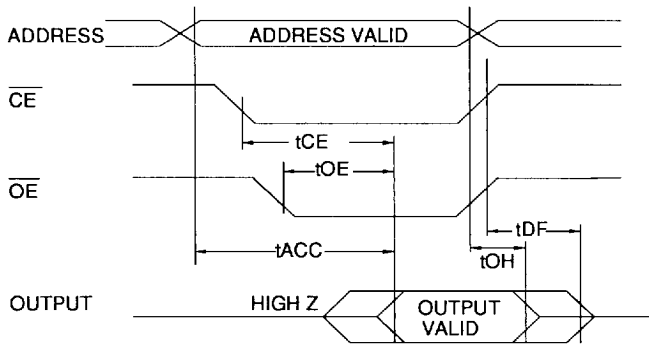
Symbol	Parameter	Condition	Min	Max	Units
I <sub>LI</sub>	Input Load Current	V <sub>IN</sub> = 0 V to V <sub>CC</sub> + 1 V		10	μA
I <sub>LO</sub>	Output Leakage Current	V <sub>I/O</sub> = 0 V to V <sub>CC</sub>		10	μA
I <sub>SB1</sub>	V <sub>CC</sub> Standby Current CMOS	$\overline{CE} = V_{CC} - 0.3 \text{ V to } V_{CC} + 1.0 \text{ V}$		100	μA
I <sub>SB2</sub>	V <sub>CC</sub> Standby Current TTL	$\overline{CE} = 2.0 \text{ V to } V_{CC} + 1.0 \text{ V}$	Com.	2	mA
			Ind., Mil.	3	mA
I <sub>CC</sub>	V <sub>CC</sub> Active Current A.C.	f = 5 MHz; I <sub>OUT</sub> = 0 mA CE = V <sub>IL</sub>	Com.	30	mA
			Ind., Mil.	45	mA
V <sub>IL</sub>	Input Low Voltage			0.8	V
V <sub>IH</sub>	Input High Voltage		2.0		V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1 mA = 4.0 mA for RDY/BUSY		.45	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -400 μA	2.4		V

A.C. Read Characteristics

Symbol	Parameter	AT28C64-12		AT28C64-15		AT28C64-20		AT28C64-25		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>ACC</sub>	Address to Output Delay	120		150		200		250		ns
t <sub>CE</sub> <sup>(1)</sup>	$\overline{CE}$ to Output Delay	120		150		200		250		ns
t <sub>OE</sub> <sup>(2)</sup>	$\overline{OE}$ to Output Delay	10	60	10	70	10	80	10	100	ns
t <sub>DF</sub> <sup>(3,4)</sup>	$\overline{CE}$ or $\overline{OE}$ High to Output Float	0	45	0	50	0	55	0	60	ns
t <sub>OH</sub>	Output Hold from $\overline{OE}$ , $\overline{CE}$ or Address, whichever occurred first	0		0		0		0		ns

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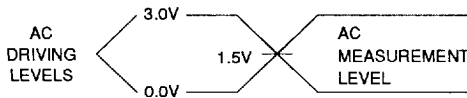
A.C. Read Waveforms



Notes:

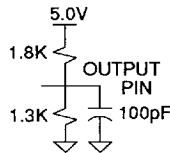
1.  $\overline{CE}$  may be delayed up to t<sub>ACC</sub> - t<sub>CE</sub> after the address transition without impact on t<sub>ACC</sub>.
2.  $\overline{OE}$  may be delayed up to t<sub>CE</sub> - t<sub>OE</sub> after the falling edge of  $\overline{CE}$  without impact on t<sub>CE</sub> or by t<sub>ACC</sub> - t<sub>OE</sub> after an address change without impact on t<sub>ACC</sub>.
3. t<sub>DF</sub> is specified from  $\overline{OE}$  or  $\overline{CE}$  whichever occurs first (C<sub>L</sub> = 5 pF).
4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



t<sub>R</sub>, t<sub>F</sub> < 20 ns

Output Test Load

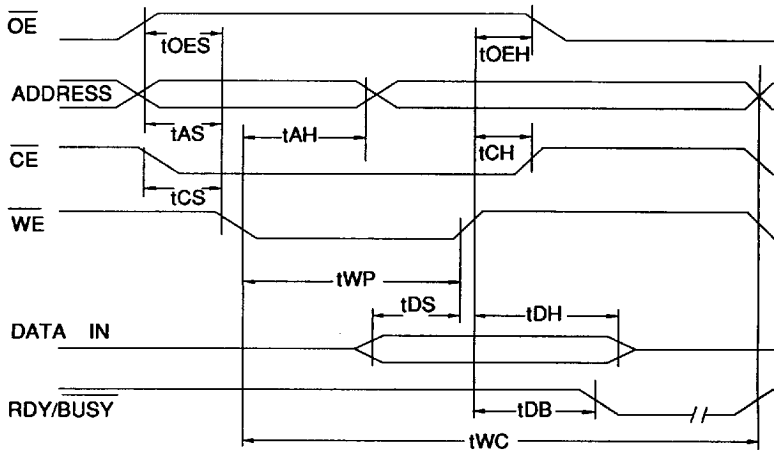


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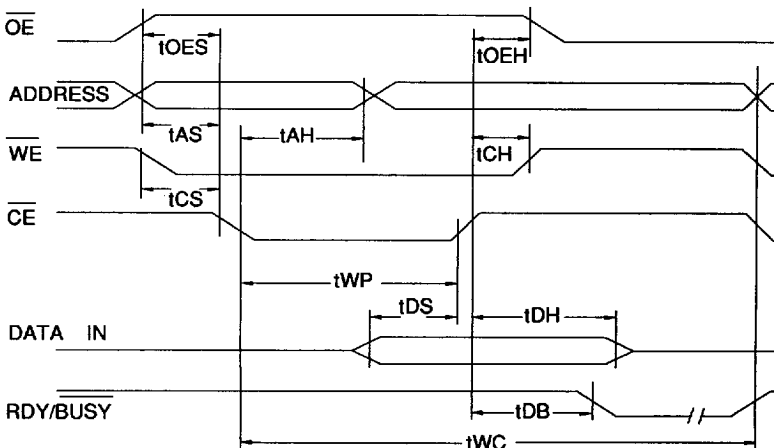
### A.C. Write Characteristics

Symbol	Parameter	Min	Typ	Max	Units
$t_{AS}, t_{OES}$	Address, $\overline{OE}$ Set-up Time	10			ns
$t_{AH}$	Address Hold Time	50			ns
$t_{WP}$	Write Pulse Width ( $\overline{WE}$ or $\overline{CE}$ )	100		1000	ns
$t_{DS}$	Data Set-up Time	50			ns
$t_{DH}, t_{OEH}$	Data, $\overline{OE}$ Hold Time	10			ns
$t_{DB}$	Time to Device Busy			50	ns
$t_{WC}$	Write Cycle Time	AT28C64	0.5	1.0	ms
		AT28C64E/F	100	200	$\mu$ s

### A.C. Write Waveforms- $\overline{WE}$ Controlled



### A.C. Write Waveforms- $\overline{CE}$ Controlled

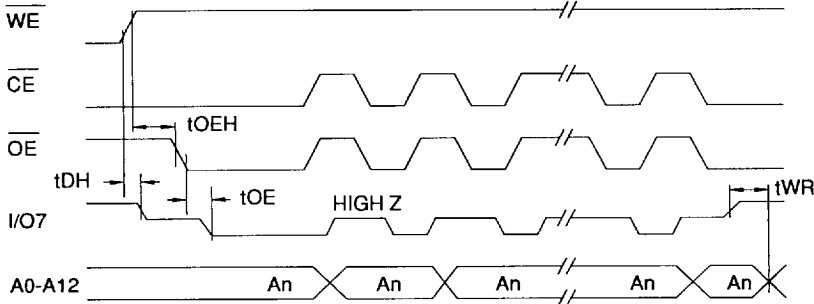


Data Polling Characteristics<sup>(1)</sup>

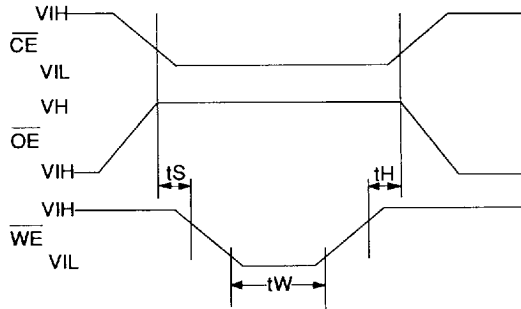
Symbol	Parameter	Min	Typ	Max	Units
t <sub>DH</sub>	Data Hold Time	10			ns
t <sub>OEH</sub>	$\overline{OE}$ Hold Time	10			ns
t <sub>OE</sub>	$\overline{OE}$ to Output Delay			100	ns
t <sub>WR</sub>	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

Data Polling Waveforms



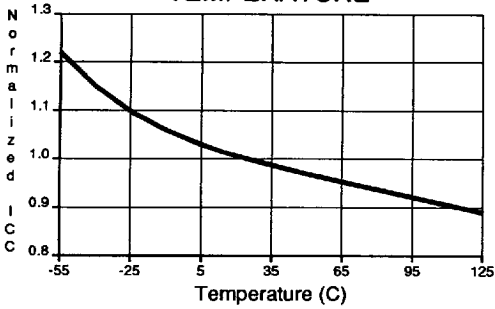
Chip Erase Waveforms



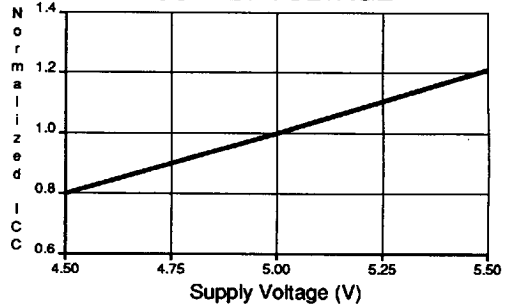
$t_S = t_H = 1 \mu\text{sec (min.)}$   
 $t_W = 10 \text{ msec (min.)}$   
 $V_H = 12.0 \text{ V} \pm 0.5 \text{ V}$



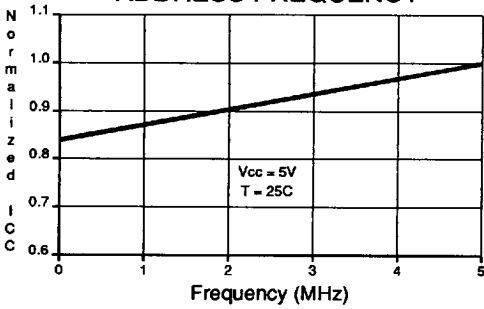
**NORMALIZED SUPPLY CURRENT vs. TEMPERATURE**



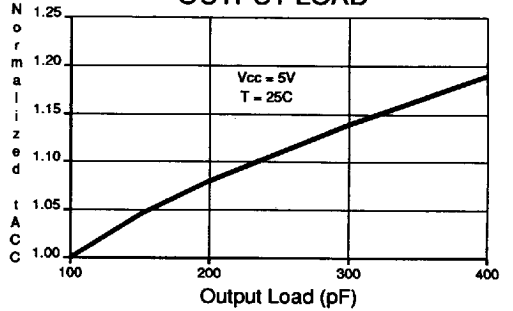
**NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE**



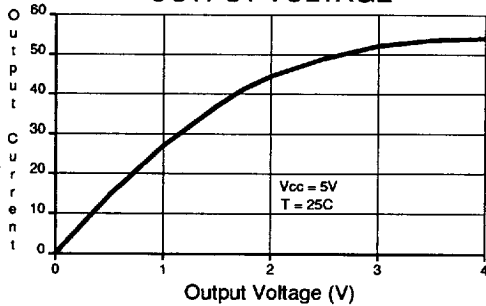
**NORMALIZED SUPPLY CURRENT vs. ADDRESS FREQUENCY**



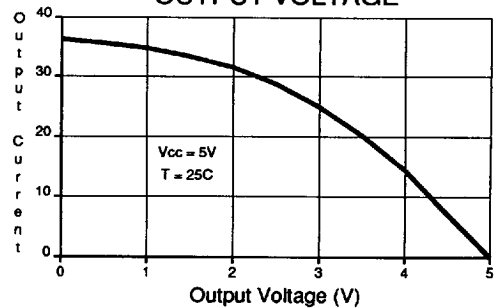
**NORMALIZED ACCESS TIME vs. OUTPUT LOAD**



**OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE**



**OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE**





Ordering Information

2

tACC (ns)	Icc (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
120	30	0.1	AT28C64(E,F)-12DC AT28C64(E,F)-12JC AT28C64(E,F)-12PC AT28C64(E,F)-12SC	28D6 32J 28P6 28S	Commercial (0°C to 70°C)
120	45	0.1	AT28C64(E,F)-12DI AT28C64(E,F)-12JI AT28C64(E,F)-12PI AT28C64(E,F)-12SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)
			AT28C64(E,F)-12DM/883 AT28C64(E,F)-12FM/883 AT28C64(E,F)-12LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
150	30	0.1	AT28C64(E,F)-15DC AT28C64(E,F)-15JC AT28C64(E,F)-15PC AT28C64(E,F)-15SC AT28C64(E,F)-15TC	28D6 32J 28P6 28S 28T	Commercial (0°C to 70°C)
150	45	0.1	AT28C64(E,F)-15DI AT28C64(E,F)-15JI AT28C64(E,F)-15PI AT28C64(E,F)-15SI AT28C64(E,F)-15TI	28D6 32J 28P6 28S 28T	Industrial (-40°C to 85°C)
			AT28C64(E,F)-15DM/883 AT28C64(E,F)-15FM/883 AT28C64(E,F)-15LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	30	0.1	AT28C64(E,F)-20DC AT28C64(E,F)-20JC AT28C64(E,F)-20PC AT28C64(E,F)-20SC	28D6 32J 28P6 28S	Commercial (0°C to 70°C)
200	45	0.1	AT28C64(E,F)-20DI AT28C64(E,F)-20JI AT28C64(E,F)-20PI AT28C64(E,F)-20SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)
			AT28C64(E,F)-20DM/883 AT28C64(E,F)-20FM/883 AT28C64(E,F)-20LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	30	0.1	AT28C64(E,F)-25DC AT28C64(E,F)-25JC AT28C64(E,F)-25PC AT28C64(E,F)-25SC AT28C64-W	28D6 32J 28P6 28S DIE	Commercial (0°C to 70°C)
250	45	0.1	AT28C64(E,F)-25DI AT28C64(E,F)-25JI AT28C64(E,F)-25PI AT28C64(E,F)-25SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)



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## Ordering Information

t <sub>acc</sub> (ns)	I <sub>cc</sub> (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
250	45	0.1	AT28C64(E,F)-25DM/883 AT28C64(E,F)-25FM/883 AT28C64(E,F)-25LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300 <sup>(1)</sup>	45	0.1	AT28C64(E,F)-30DM/883 AT28C64(E,F)-30FM/883 AT28C64(E,F)-30LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350 <sup>(1)</sup>	45	0.1	AT28C64(E,F)-35DM/883 AT28C64(E,F)-35FM/883 AT28C64(E,F)-35LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
150	45	0.1	5962-87514 17 XX 5962-87514 17 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	45	0.1	5962-87514 16 XX 5962-87514 16 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	45	0.1	5962-87514 15 XX 5962-87514 15 YX 5962-87514 15 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300 <sup>(1)</sup>	45	0.1	5962-87514 14 XX 5962-87514 14 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350 <sup>(1)</sup>	45	0.1	5962-87514 13 XX 5962-87514 13 YX 5962-87514 13 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Notes: 1. Electrical specifications for these speeds are defined in Standardized Military Drawing 5962-87514.

Package Type	
<b>28D6</b>	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)
<b>28F</b>	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)
<b>32J</b>	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
<b>32L</b>	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
<b>28P6</b>	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
<b>28S</b>	28 Lead, 0.300" Wide, Plastic Gull Wing, Small Outline (SOIC)
<b>28T</b>	28 Lead, Plastic Thin Small Outline Package (TSOP)
<b>W</b>	Die
Options	
<b>Blank</b>	Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms
<b>E</b>	High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 μs
<b>F</b>	Fast Write Option: Write Time = 200 μs

2-100

**AT28C64/X**

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**Ordering Information**

t <sub>ACC</sub> (ns)	I <sub>CC</sub> (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
150	30	0.1	AT28C64X-15DC AT28C64X-15FC AT28C64X-15JC AT28C64X-15PC AT28C64X-15SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)
150	45	0.1	AT28C64X-15DI AT28C64X-15FI AT28C64X-15JI AT28C64X-15PI AT28C64X-15SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)
			AT28C64X-15DM/883 AT28C64X-15FM/883 AT28C64X-15LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	30	0.1	AT28C64X-20DC AT28C64X-20FC AT28C64X-20JC AT28C64X-20PC AT28C64X-20SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)
200	45	0.1	AT28C64X-20DI AT28C64X-20FI AT28C64X-20JI AT28C64X-20PI AT28C64X-20SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)
			AT28C64X-20DM/883 AT28C64X-20FM/883 AT28C64X-20LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	30	0.1	AT28C64X-25DC AT28C64X-25FC AT28C64X-25JC AT28C64X-25PC AT28C64X-25SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)
250	45	0.1	AT28C64X-25DI AT28C64X-25FI AT28C64X-25JI AT28C64X-25PI AT28C64X-25SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)
			AT28C64X-25DM/883 AT28C64X-25FM/883 AT28C64X-25LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	45	0.1	AT28C64X-30DM/883 AT28C64X-30FM/883 AT28C64X-30LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	45	0.1	AT28C64X-35DM/883 AT28C64X-35FM/883 AT28C64X-35LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)

2



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## Ordering Information

t <sub>ACC</sub> (ns)	I <sub>CC</sub> (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
150	45	0.1	5962-87514 22 XX 5962-87514 22 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	45	0.1	5962-87514 21 XX 5962-87514 21 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	45	0.1	5962-87514 20 XX 5962-87514 20 YX 5962-87514 20 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	45	0.1	5962-87514 19 XX 5962-87514 19 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	45	0.1	5962-87514 18 XX 5962-87514 18 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type	
<b>28D6</b>	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual In-line Package (Cerdip)
<b>28F</b>	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)
<b>32J</b>	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
<b>32L</b>	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
<b>28P6</b>	28 Lead, 0.600" Wide Plastic Dual In-line Package (PDIP)
<b>28S</b>	28 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)

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